ABSTRACT OF THE DISCLOSURE

The invention encompasses a method of forming silicon nitride on a silicon-oxide-comprising material. The silicon-oxide-comprising material is exposed to activated nitrogen species from a nitrogen-containing plasma to introduce nitrogen into an upper portion of the material. The nitrogen is thermally annealed within the material to bond at least some of the nitrogen to silicon proximate the nitrogen. After the annealing, silicon nitride is chemical vapor deposited on the nitrogen-containing upper portion of the material. The invention also encompasses a method of forming a transistor device. A silicon-oxide-comprising layer is formed over a substrate. The silicon-oxide-comprising layer is exposed to nitrogen from a nitrogen-containing plasma to introduce nitrogen into an upper portion of the layer. The nitrogen is thermally annealed within the layer to bond at least some of the nitrogen silicon proximate the nitrogen. After the annealing, silicon nitride is chemical vapor deposited on the nitrogen-containing upper portion of the layer. At least one conductive gate layer is formed over the silicon nitride, and defines a gate layer. A pair of source/drain regions are formed proximate the gate layer and gatedly connected to one another through a channel region that is beneath the gate layer. Additionally, the invention encompasses transistor device structures.